

/ Descriptions

Silicon PNP transistor in a TO-252 Plastic Package.

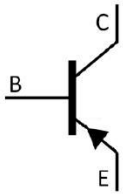
/ Features

High voltage.

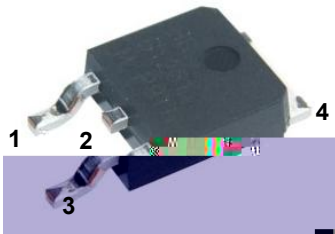
/ Applications

High voltage general purpose applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2,4 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

See Marking Instructions.

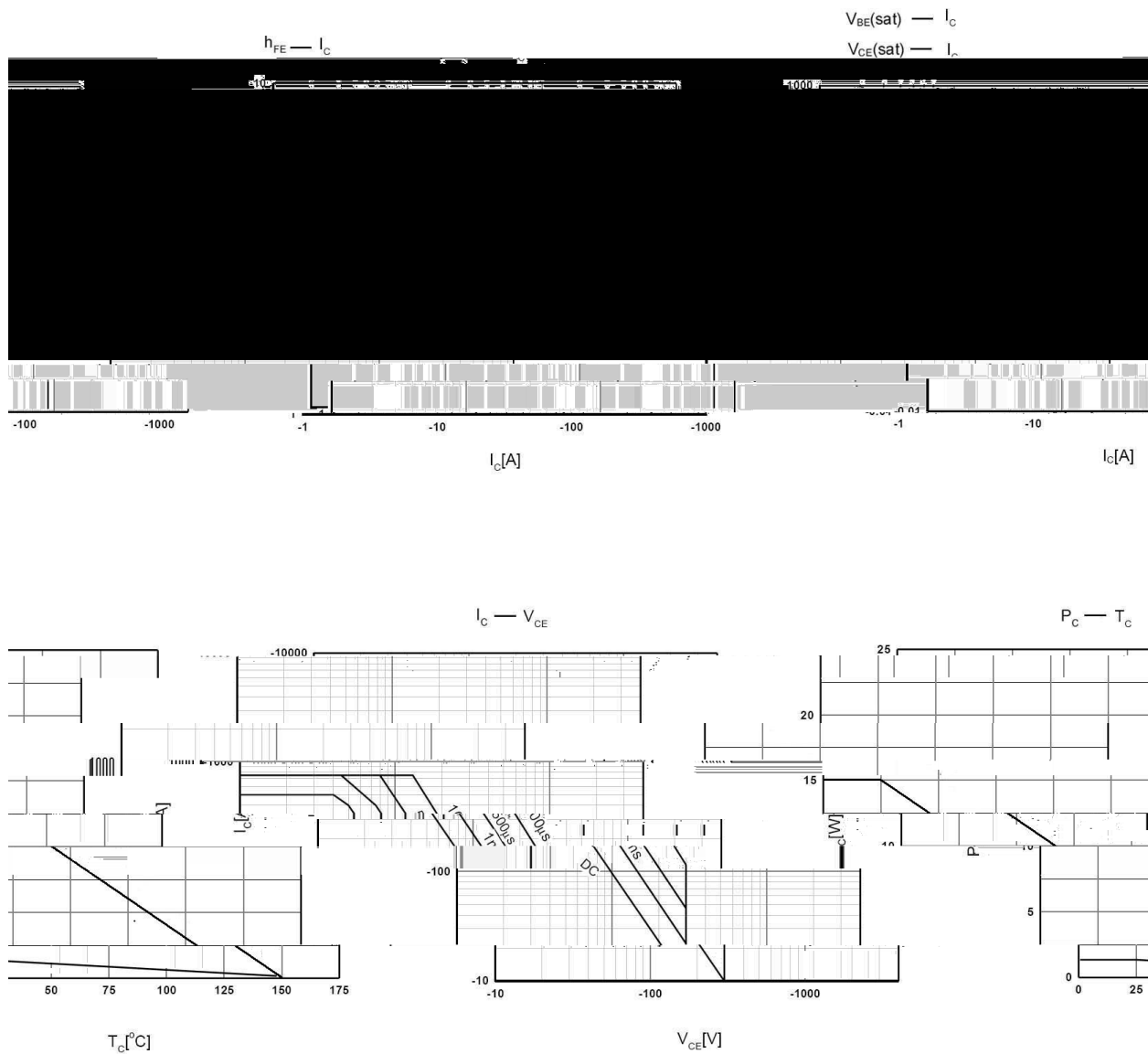
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-300	V
Collector to Emitter Voltage	V_{CEO}	-300	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-500	mA
Collector Power Dissipation	P_C	1.56	W
Collector Power Dissipation	$P_C(T_C=25^{\circ}C)$	15	W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55 150	$^{\circ}C$

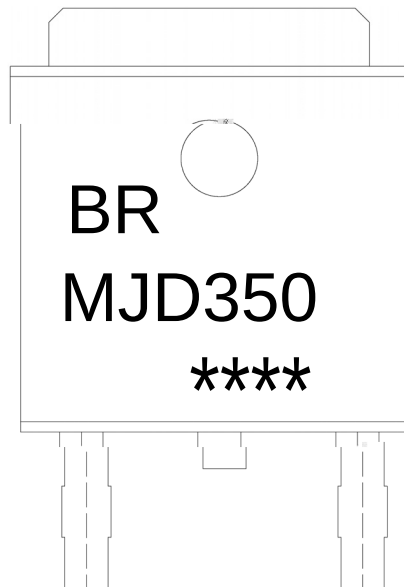
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-0.1mA$ $I_E=0$	-300			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-1mA$ $I_B=0$	-300			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_C=-0.1mA$ $I_B=0$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-300V$ $I_E=0$			-100	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-3V$ $I_C=0$			-100	A
DC Current Gain	h_{FE}	$V_{CE}=-10V$ $I_C=-50mA$	30		240	

/ **Electrical Characteristic Curve**



/ **Marking Instructions**



BR

Note:

BR: Company Code

MJD350: Product Type.

****: Lot No. Code, code change with Lot No.

